

Switching diode

- Applications**

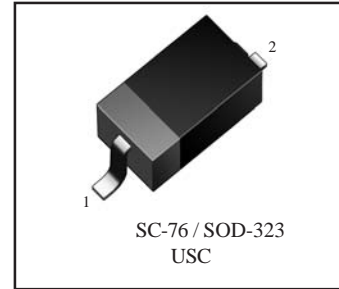
High speed switching

- Features**

- 1) Small surface mounting type.
- 2) High Speed. ($t_{rr} = 1.2\text{ns Typ.}$)
- 3) High reliability with high surge current handling capability.
- 4) Pb-Free package is available.

- Construction**

Silicon epitaxial planar



- Device Marking and Ordering Information**

Device	Marking	Shipping
1N4148WS	HA2	3000/Tape&Reel

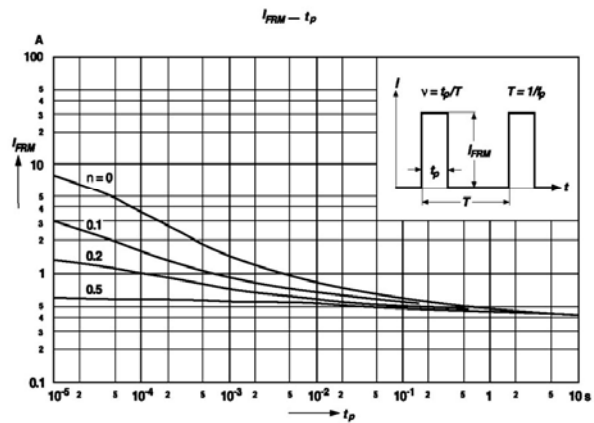
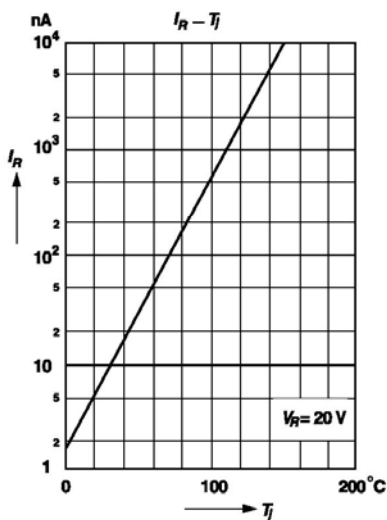
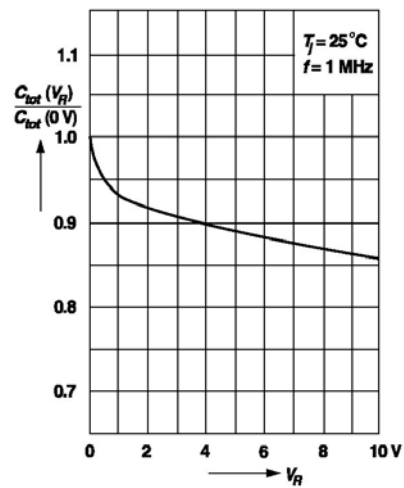
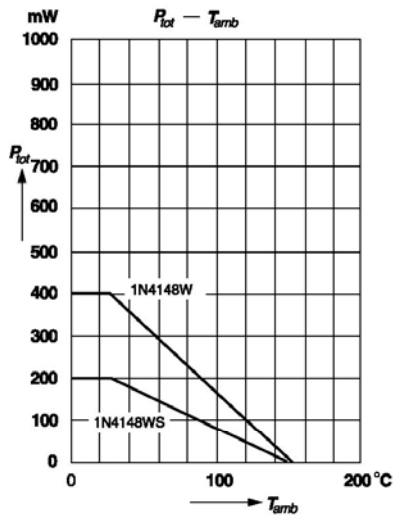
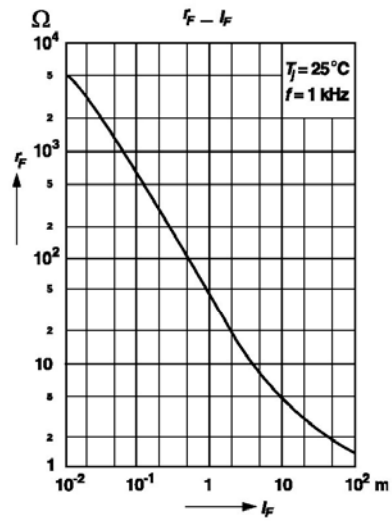
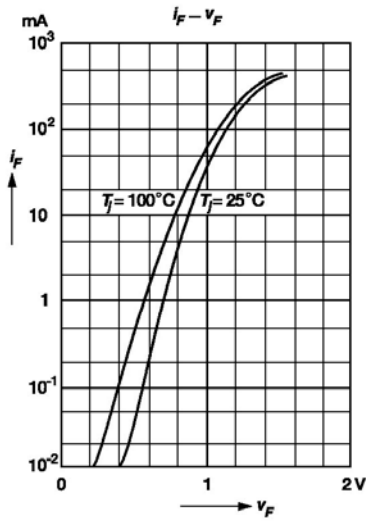
ABSOLUTE MAXIMUM RATINGS ($T_a = 25\text{ C}$)

Parameter	Symbol	Limit	Unit
Peak reverse voltage	V_{RM}	100	V
DC reverse voltage	V_R	75	V
Peak forward current	I_{FM}	300	mA
Mean rectifying current	I_O	150	mA
Surge current (1s)	I_{surge}	1	A
Power Dissipation	P_D	200	mW
Junction temperature	T_J	150	C
Storage temperature	T_{sg}	- 55 ~ +150	C

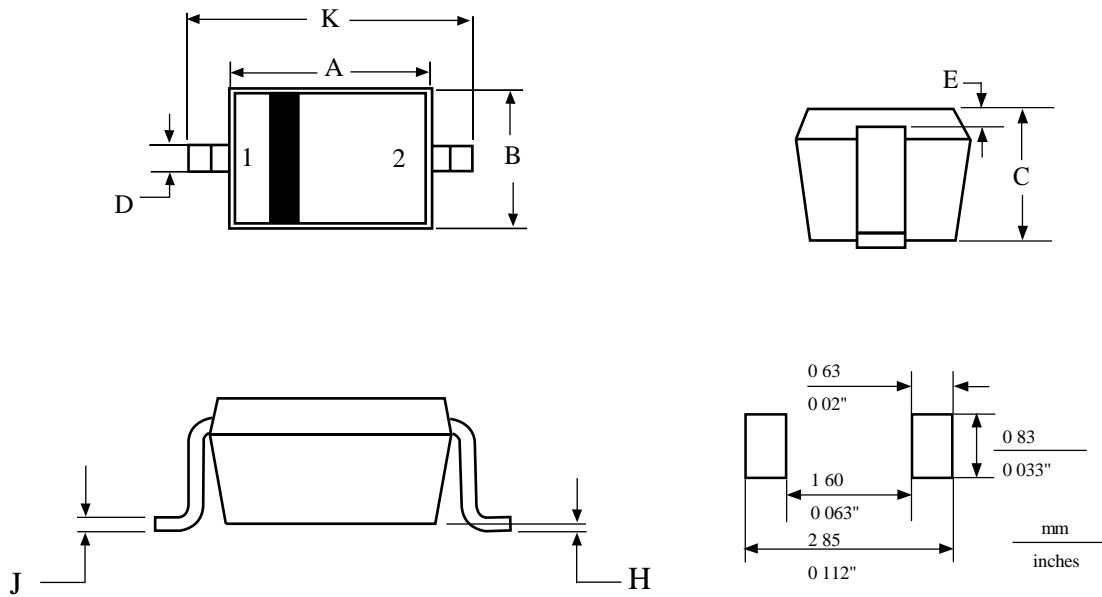
ELECTRICAL CHARACTERISTICS ($T_a = 25\text{ C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)}$	100			V	$I_R=100\mu\text{A}$
Forward voltage	V_F			1.0	V	$I_F=10\text{mA}$
Reverse current	I_R			25	nA	$V_R=20\text{V}$
				5.0	μA	$V_R=75\text{V}$
Capacitance between terminals	C_T			4.0	pF	$V_R=0\text{V}, f=1.0\text{MHz}$
Reverse Recovery Time	t_{rr}			4	ns	$I_F=I_R=10\text{mA}$

ELECTRICAL CHARACTERISTIC CURVES



SC-76 / SOD-323



NOTES:

1. DIMENSIONING AND TOLERANCING

PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: MILLIMETERS

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.60	1.80	0.063	0.071
b	1.15	1.35	0.045	0.053
C	0.80	1.00	0.031	0.039
D	0.25	0.40	0.010	0.016
E	0.15 REF		0.006 REF	
H	0.00	0.10	0.000	0.004
J	0.089	0.177	0.0035	0.0070
K	2.30	2.70	0.091	0.106

PIN:1:CATHODE

2:ANODE